

N-Channel 700 V(D-S) Power MOSFET

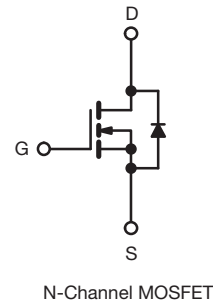
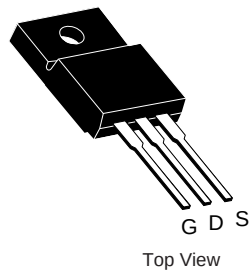

RoHS
 COMPLIANT

PRODUCT SUMMARY		
V_{DS} (V)	700	
$R_{DS(on)}$ max. (Ω) at 25 °C	$V_{GS} = 10$ V	1.4
Q_g Typ. (nC)	24	
Q_{gs} (nC)	6	
Q_{gd} (nC)	11	
Configuration	Single	

FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Compliant to RoHS directive 2002/95/EC

TO-220 FULLPAK



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V _{DS}	700	V
Gate-source voltage			V _{GS}	± 30	
Continuous drain current (T _J = 150 °C) ^e	V _{GS} at 10 V	T _C = 25 °C	I _D	7	A
		T _C = 100 °C		5	
Pulsed drain current ^a			I _{DM}	18	
Linear derating factor				0.63	W/°C
Single pulse avalanche energy ^b			E _{AS}	56	mJ
Maximum power dissipation			P _D	31	W
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +150	°C
Drain-source voltage slope	T _J = 125 °C		dV/dt	37	V/ns
Reverse diode dV/dt ^d		27			
Soldering recommendations (peak temperature) ^c	For 10 s			300	°C
Mounting torque	M3 screw			0.6	Nm

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 2$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C
- Limited by maximum junction temperature

THERMAL RESISTANCE RATINGS

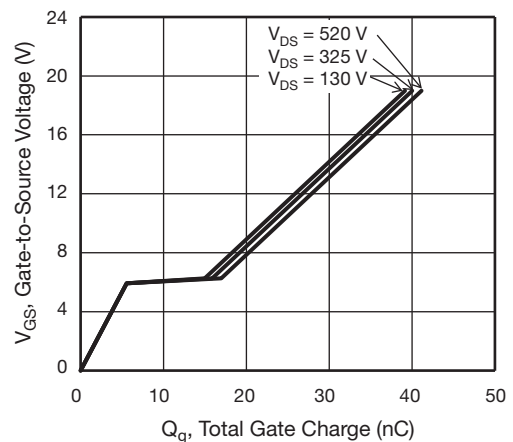
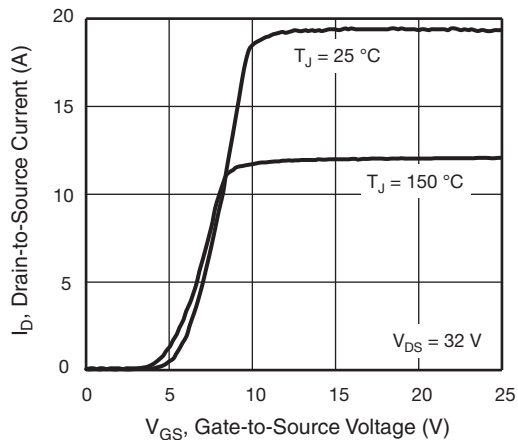
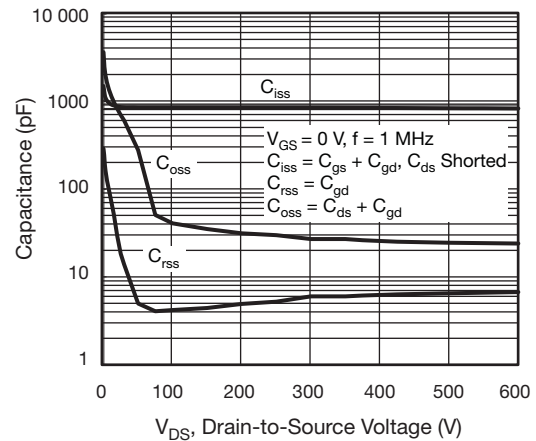
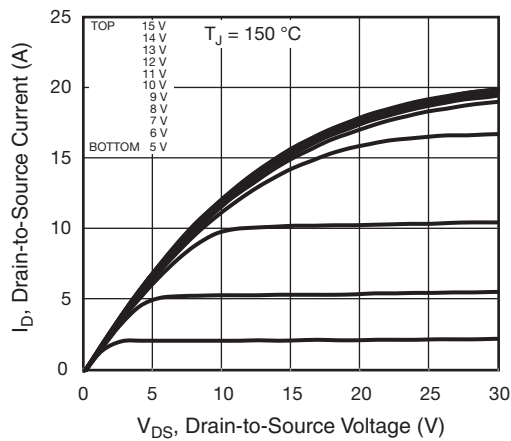
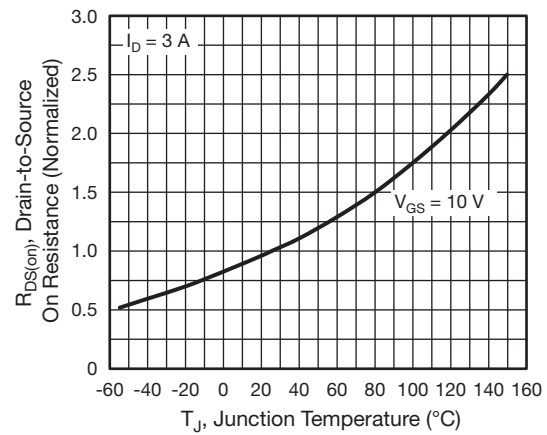
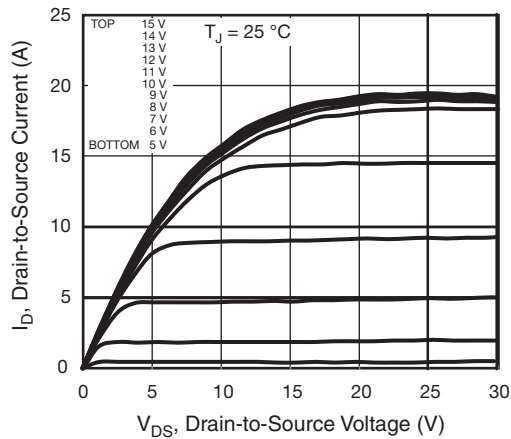
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	43	65	°C/W
Maximum junction-to-case (drain)	R_{thJC}	3.1	4.0	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	700	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$	-	0.73	-	V/ $^{\circ}\text{C}$
Gate-source threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	-	4	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$	-	-	± 1	μA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 700\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 560\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$	-	1.36	-	Ω
Forward transconductance	g_{fs}	$V_{DS} = 30\text{ V}$, $I_D = 3\text{ A}$	-	2	-	S
Dynamic						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$	410	820	-	pF
Output capacitance	C_{oss}		20	60	-	
Reverse transfer capacitance	C_{rss}		2	4	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 560\text{ V}$, $V_{GS} = 0\text{ V}$	-	36	-	
Effective output capacitance, time related ^b	$C_{o(tr)}$		-	117	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $V_{DS} = 520\text{ V}$	-	24	48	nC
Gate-source charge	Q_{gs}		-	6	-	
Gate-drain charge	Q_{gd}		-	11	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 560\text{ V}$, $I_D = 3\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 9.1\text{ }\Omega$	-	14	28	ns
Rise time	t_r		-	12	24	
Turn-off delay time	$t_{d(off)}$		-	30	60	
Fall time	t_f		-	20	40	
Gate input resistance	R_g	$f = 1\text{ MHz}$, open drain	0.4	1.4	2.7	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	7	A
Pulsed diode forward current	I_{SM}		-	-	18	
Diode forward voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 3\text{ A}$, $V_{GS} = 0\text{ V}$	-	0.83	1.3	V
Reverse recovery time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 25\text{ V}$	118	237	474	ns
Reverse recovery charge	Q_{rr}		-	2.2	-	μC
Reverse recovery current	I_{RRM}		-	16	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


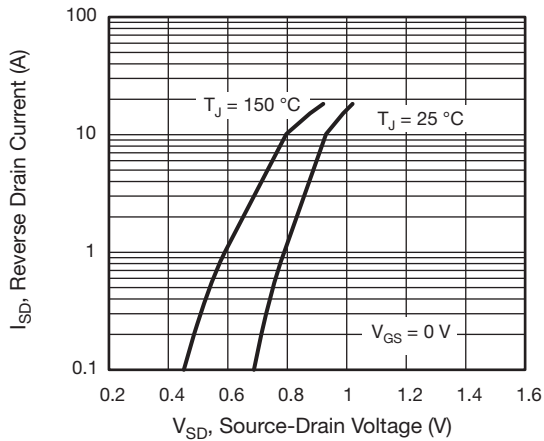


Fig. 7 - Typical Source-Drain Diode Forward Voltage

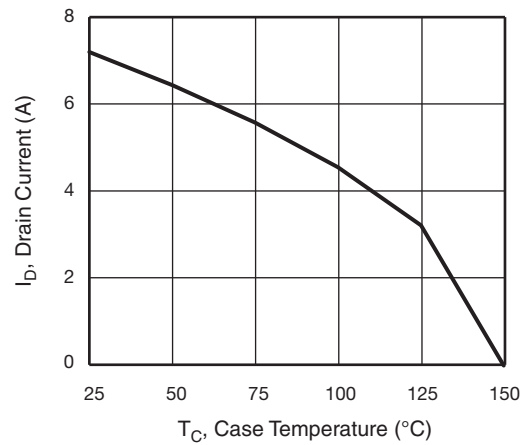


Fig. 9 - Maximum Drain Current vs. Case Temperature

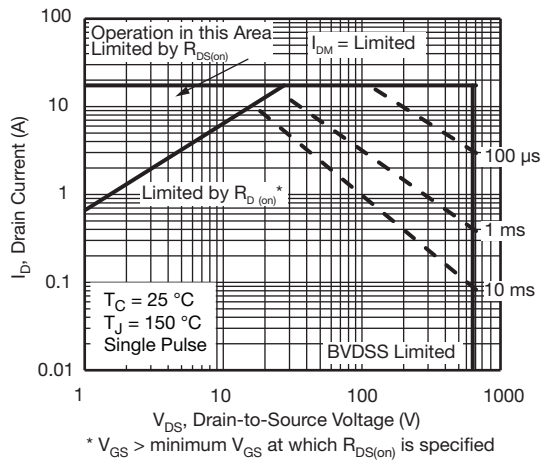


Fig. 8 - Maximum Safe Operating Area

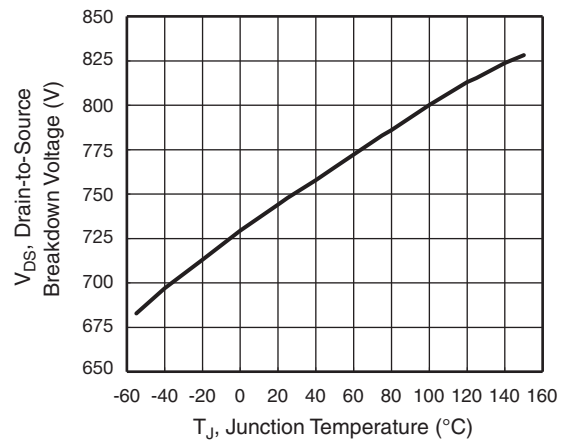


Fig. 10 - Temperature vs. Drain-to-Source Voltage

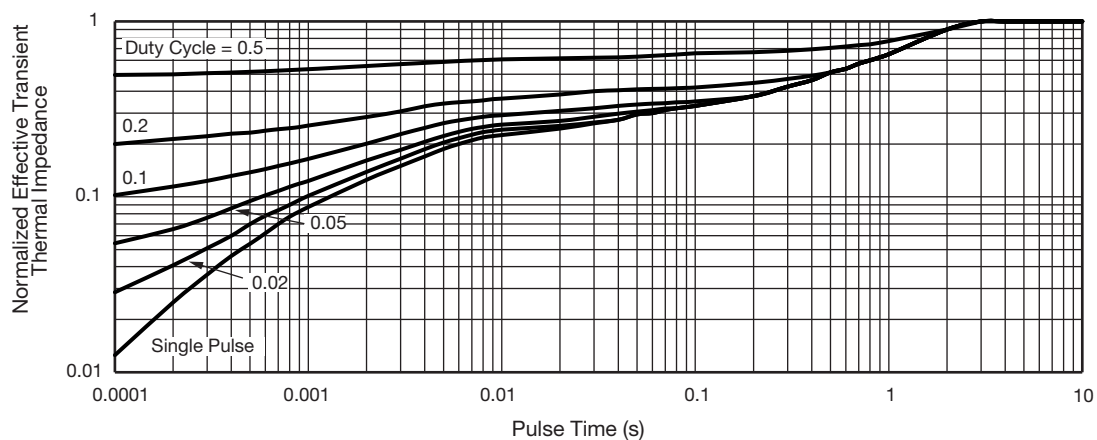


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

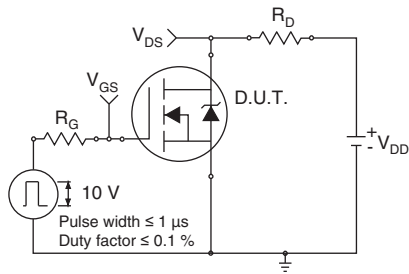


Fig. 12 - Switching Time Test Circuit

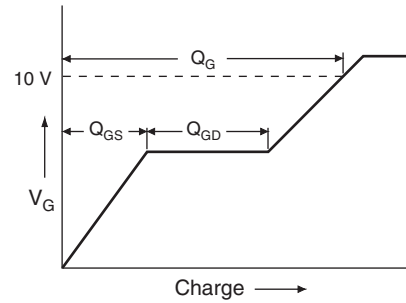


Fig. 16 - Basic Gate Charge Waveform

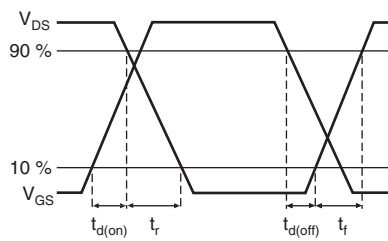


Fig. 13 - Switching Time Waveforms

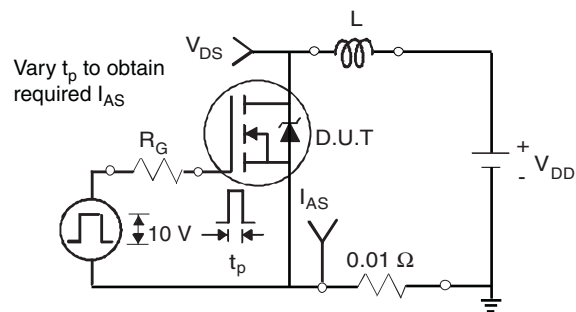


Fig. 14 - Unclamped Inductive Test Circuit

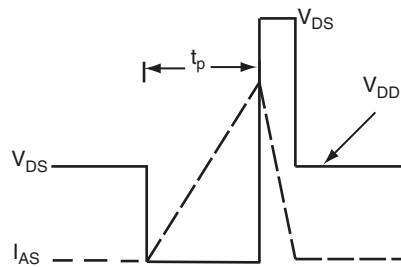


Fig. 15 - Unclamped Inductive Waveforms

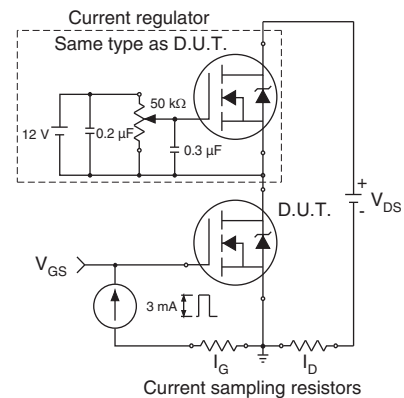
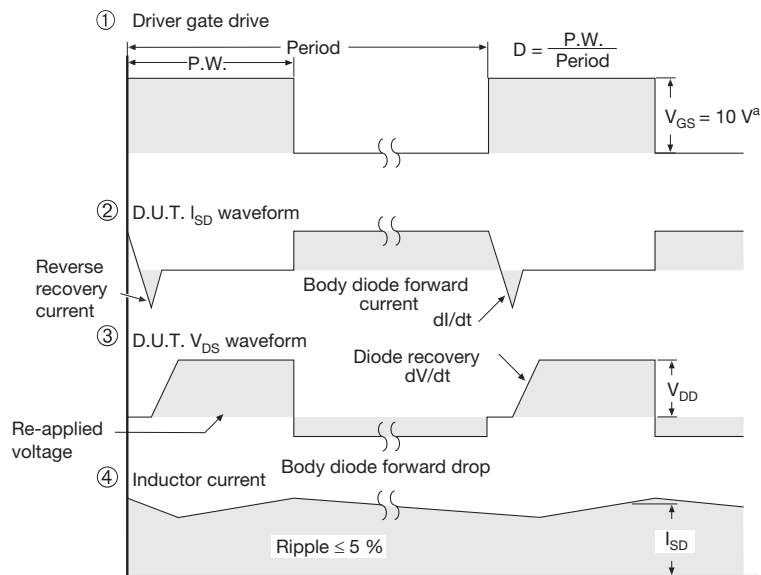
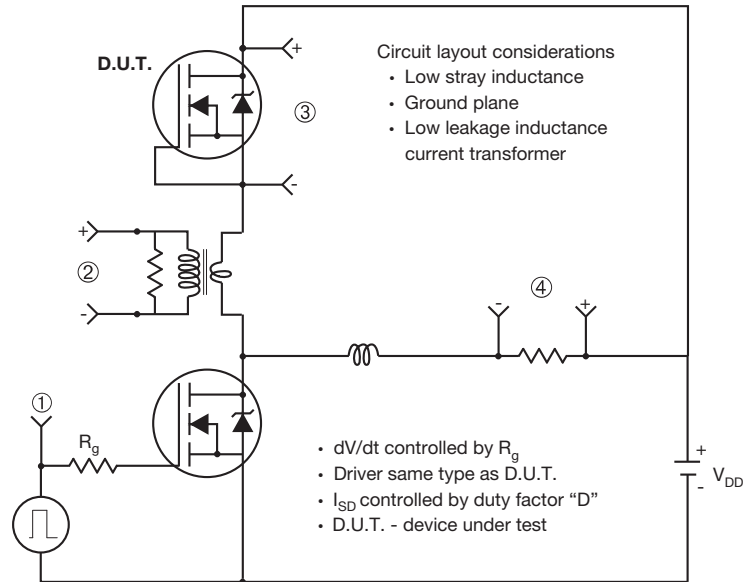
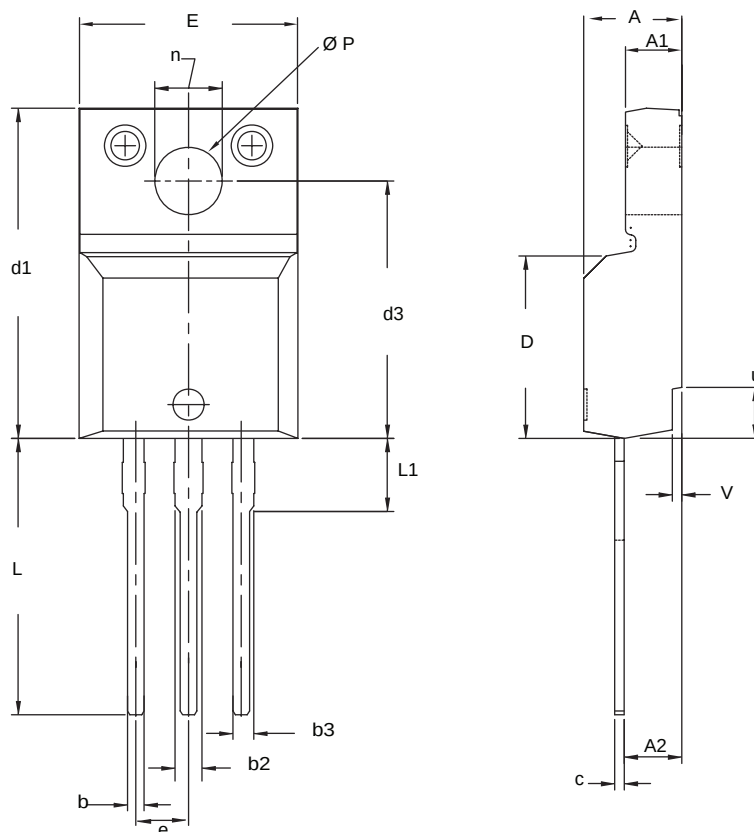


Fig. 17 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit**Note**

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

TO-220 FULL PAK (HIGH VOLTAGE)

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
 DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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